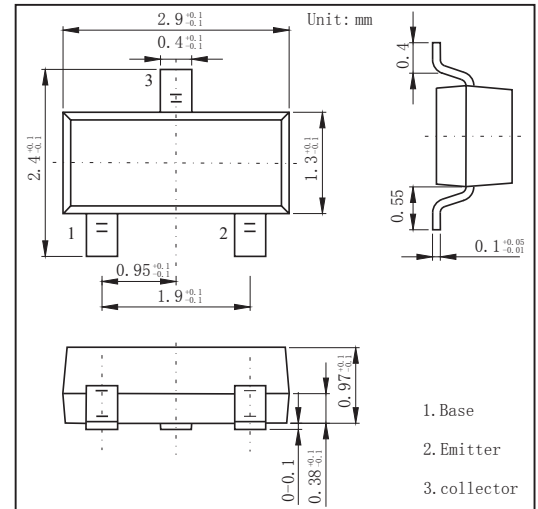


SOT-23 Plastic-Encapsulate Transistors
FEATURES

- High hFE
- Low VCE(sat)
- For general amplification
- NPN Transistors

MECHANICAL DATA

- Case style: SOT-23 molded plastic
- Mounting position: any


MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	VCBO	60	V
Collector - Emitter Voltage	VCEO	50	
Emitter - Base Voltage	VEBO	7	
Collector Current - Continuous	IC	100	mA
Collector Power Dissipation	PC	200	mW
Thermal Resistance from Junction to Ambient	RθJA	625	°C/W
Junction Temperature	TJ	150	°C
Storage Temperature Range	Tstg	-55 to +150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	VCBO	Ic= 100 μA, IE= 0	60			V
Collector- emitter breakdown voltage	VCEO	Ic= 2 mA, IB= 0	50			
Emitter - base breakdown voltage	VEBO	IE= 100 μA, IC= 0	7			
Collector-base cut-off current	ICBO	VCB= 50 V, IE= 0			0.1	uA
Collector-emitter cut-off current	ICEO	VCE= 30 V, IB= 0			100	
Emitter cut-off current	IEBO	VEB= 5V, Ic=0			0.1	
Collector-emitter saturation voltage	VCE(sat)	Ic=100 mA, IB=10mA			0.3	V
Base - emitter saturation voltage	VBE(sat)	Ic=100 mA, IB=10mA			1.2	
DC current gain	hFE(1)	VCE= 2V, Ic= 100mA	90			
	hFE(2)	VCE= 10V, Ic= 2mA	160		460	
Collector output capacitance	Cob	VCB= 10V, IE=0,f=1MHz		3.5		pF
Transition frequency	ft	VCE= 10V, Ic= 2mA,f=200MHz		150		MHz